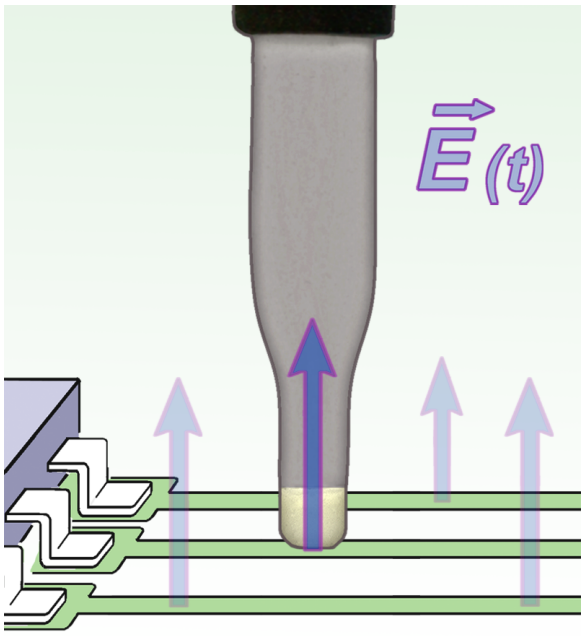
XF-E 10

E-Field Probe 30 MHz up to 6 GHz



Short description

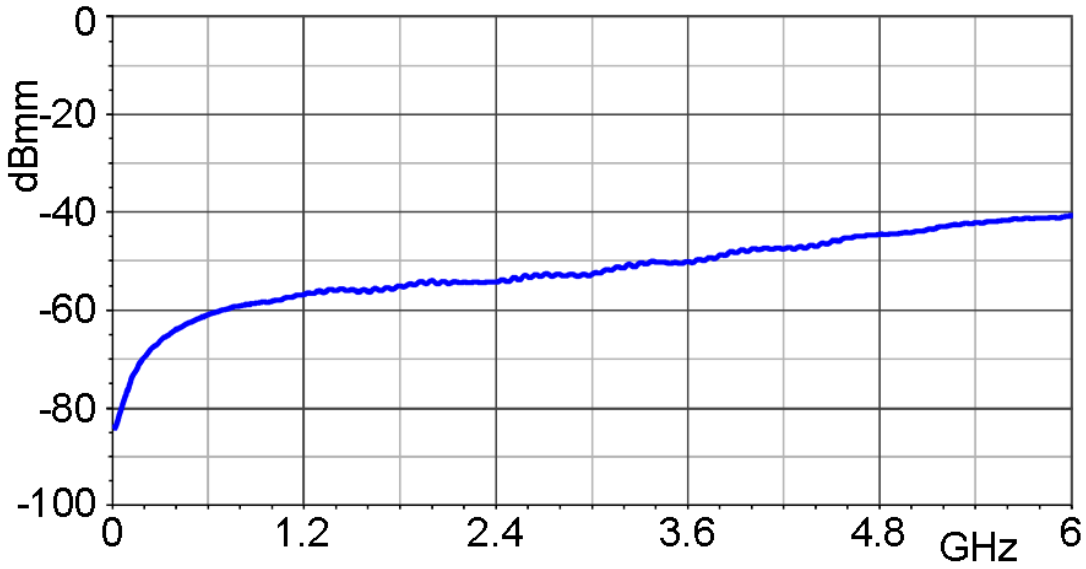
The electrode in the probe head of the XF-E 10 has a width of approx. 0.2 mm. With the probe even smallest E-field sources can be located, e.g. conducting paths with a width of 0.1 mm or single pins on multi pinned ICs. To measure, the E-field probe is positioned onto the object.

The XF-E 10 probe is a passive near-field probe. In principle it has the same structure as the XF-E 04 and XF-E 09 probes. The resolution of XF-E 10, however, is significantly higher. Normally the probe head is positioned directly onto the measured object (high electric field strength). It is not suitable for measurements from greater distances, which can be done using the XF-E 04 or XF-E 09. The near-field probe is small and handy. It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The H-field probe has an internal terminating resistance.

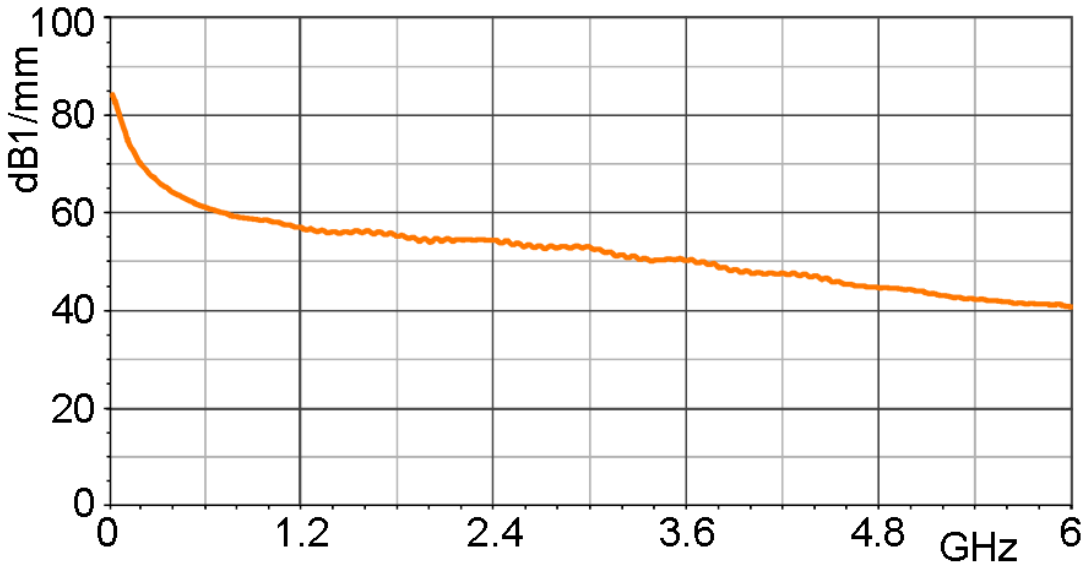
Technical parameters

Frequency range	30 MHz ... 6 GHz
Resolution	≈ 0.2 mm
Probe head dimensions:	≈ (0.5 x 2) mm
Connector - output	SMA, female, jack
Weight	15 g

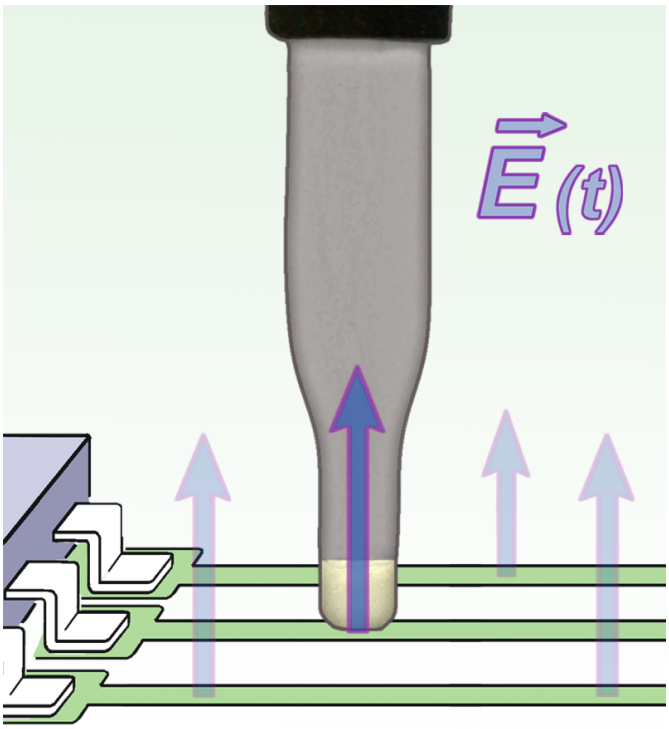
Frequency response [dBµV] / [dBµV/mm]



E- field correction curve [dBµV/mm] / [dBµV]



Measuring principles



Probe head